IBM Research

Effect of impurity on Cu electromigration

C.K. Hu, M. Angyal, B. Baker, G. Bonilla, C. Cabral, D. F. Canaperi, L. Clevenger, D. Edelstein, L. Gignac, E. Huang, J. Kelly, B. Y. Kim, V. Kyei-Fordjour, S. L. Manikonda, J. Maniscalco, S. Mittal, T. Nogami, C. Parks, R. Rosenberg , A. Simon T. Y. Su, A Vo, C. Witt

This work was performed by the Research Alliance Teams at various IBM Research and Development Facilities

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Outline

- **Electromigration Roadmap**
  - EM scaling rule
- **Improve EM techniques:**
  - e-plating chemistry, alloy, alternative liner, metal cap
  - Modify Cu surface
- **Solute effect on Cu EM**
  - Electroplating chemicals (S, Cl, C, O)
  - Alloy seed: Cu(Ti), Cu(Al), Cu(Sn), Cu(Zr), Cu(In)
  - Liner: PVD Ti(Ta), CVD Co, CVD Ru, PVD Ru
  - Metal cap: CoWP, CVD Ru
- **Conclusions**

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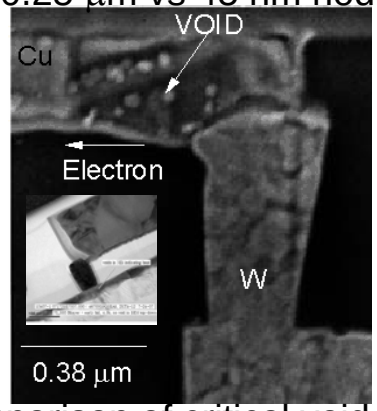
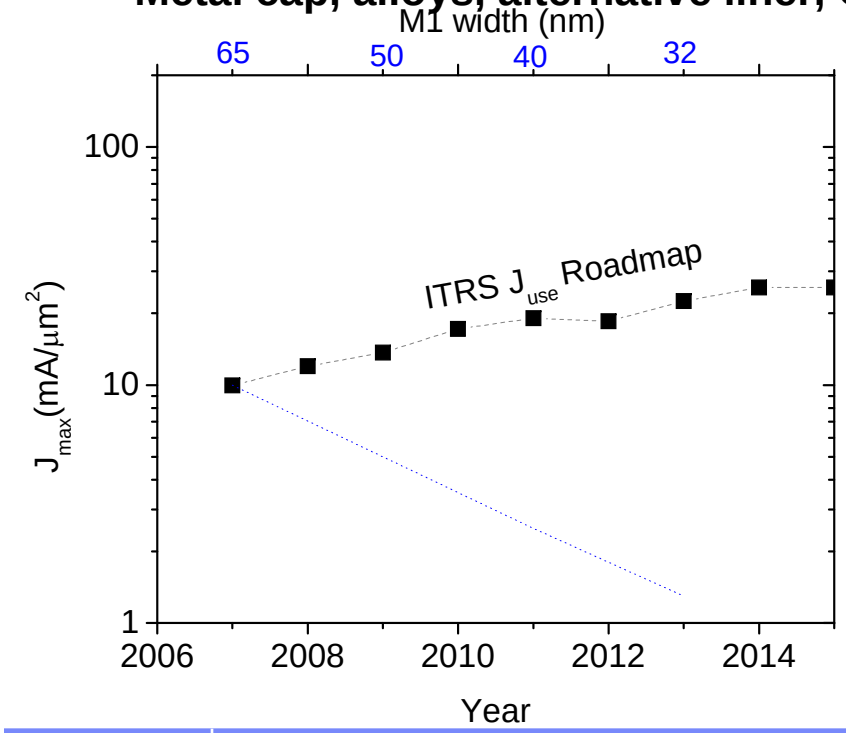
EM Roadmap

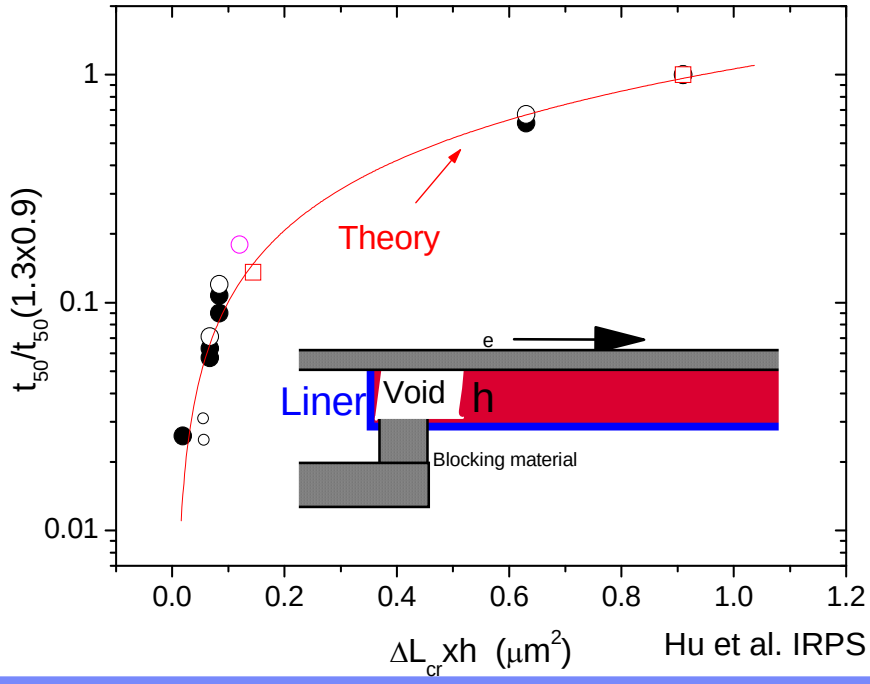
- **Scaling challenges:**
  - Increasing difficulty to fabricate reliable wafers
  - Lifetime degradation with technology scaling limits design scaling
    - Fraction of atoms on fast diffusion path increases
    - Fatal void volume decreases – shorter time to failure
    - Increasing polycrystalline sections in Cu lines: more fast paths
    - Juse drops by half in every new generation
  - Need to pursue techniques for EM enhancement
    - **Metal cap, alloys, alternative liner, Cu surface modification**

0.25 μm vs 45 nm node



Comparison of critical void volume





Hu et al. IRPS '04

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Diffusion Path in Cu Damascene Interconnections

EM drift velocity (mass flow) = $(\mathbf{D_{eff}}/KT)F_e$

1. Interface Diffusion:
   - D_i: Cu/Ta (0.7 or 1.4, or >1.8 eV)
   - **D_s: Cu/SiCNH (0.8-1 eV)**
2. Grain boundary Diffusion
   - **D_{gb} (0.75-0.87 eV)** *(Surholt & Herzig, Acta mater. '97)*

❑ Cu mass flow:

❖Polycrystalline line structure

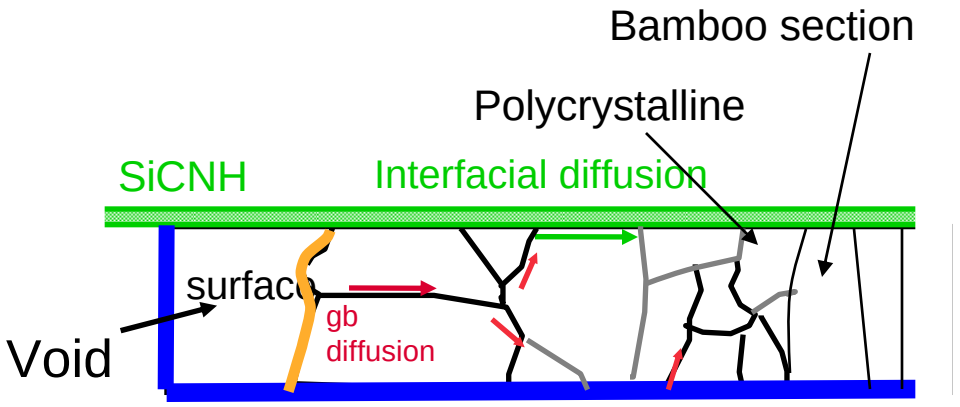
$$v_d = [(\delta_{gb}/d)D_{gb}Z_{gb}^*]e\rho j/kT$$

❖Bamboo-like line structure

$$v_d = [\delta_S(1/h)D_SZ_S^*]e\rho j/kT$$

❖Bamboo/polycrystalline line structure

$$v_d = A[D_{eff}Z_{eff}^*]e\rho j/kT$$



~Drift velocity of bamboo-like line, if length of polycrystalline section < Blech Short Length

~ function of bamboo and polycrystalline sections

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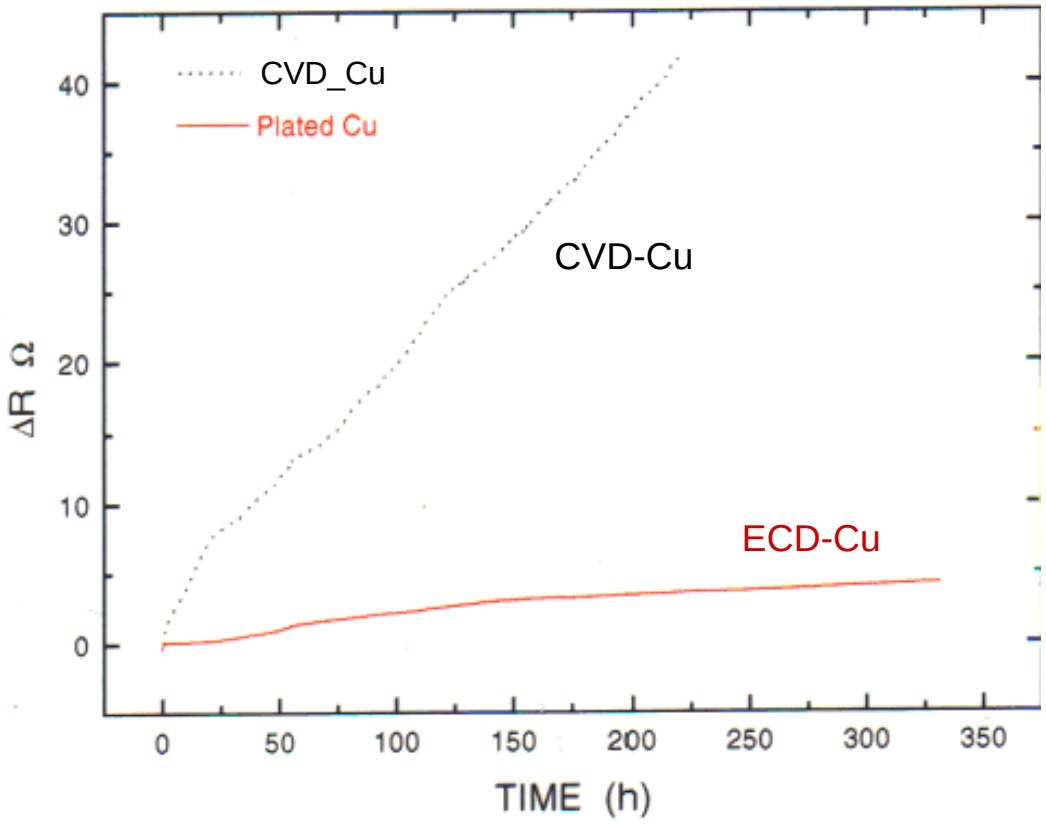
Solute Effect: Non-metallic impurities

Discovery of Superior EM Reliability of ECD-Cu in 1992

- ECD-Cu has a better activation energy and lifetimes than PVD- and CVD-Cu
  - Attribute this superior EM to microstructure and/or impurity
  - ← ECD-Cu has a larger Cu grain size
  - ← ECD-Cu has more impurities, such as Cl, C, O, S



Electromigration activation energy

CVD Cu 0.7-0.8 eV

Plated Cu 1.1-1.3 eV

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Non-metallic impurities

M. Stangl et al. Thin Sold Films, 517, 2687 (2009)

- Two electroplated solutions (A & B): Solute concentration in B is 10x of A
  - Indicates **higher impurity degrades** EM lifetime and activation energy

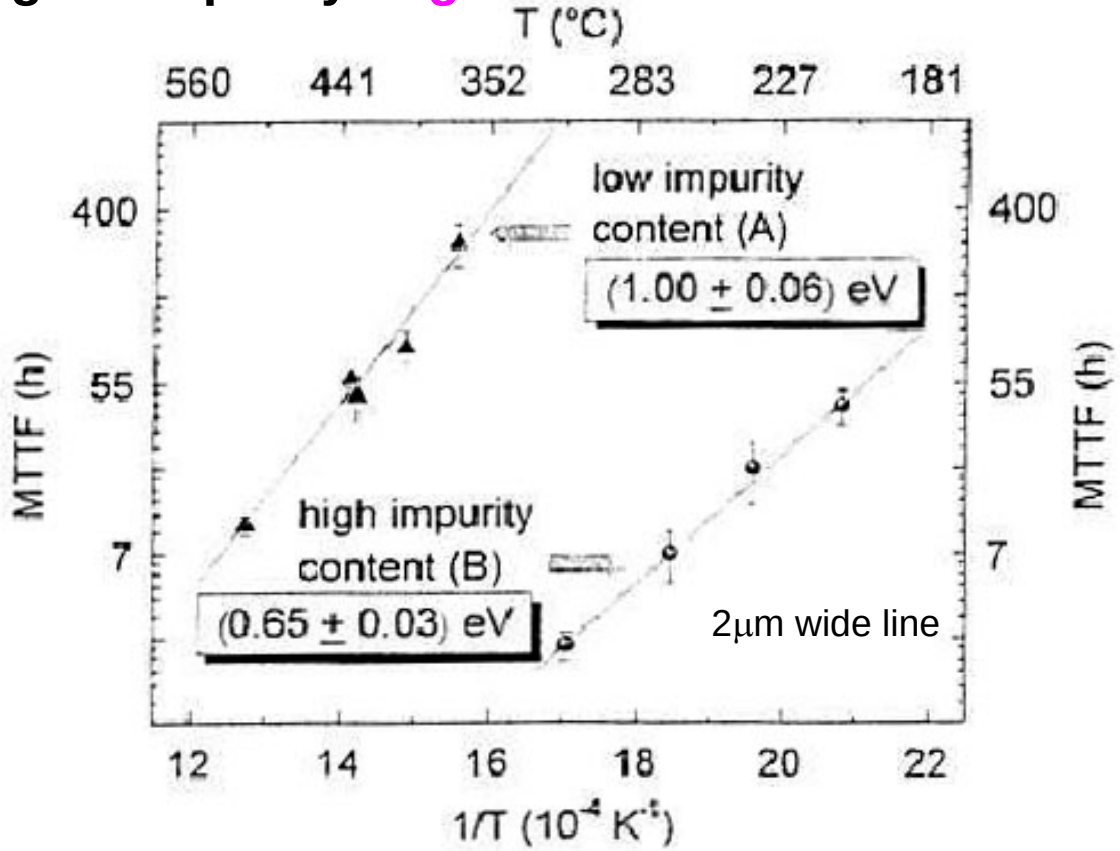

Fig. 5. Lifetime vs. (1/T) with extracted values for EM activation energy for Cu interconnect lines with low (A) and high (B) content of non-metal impurities.

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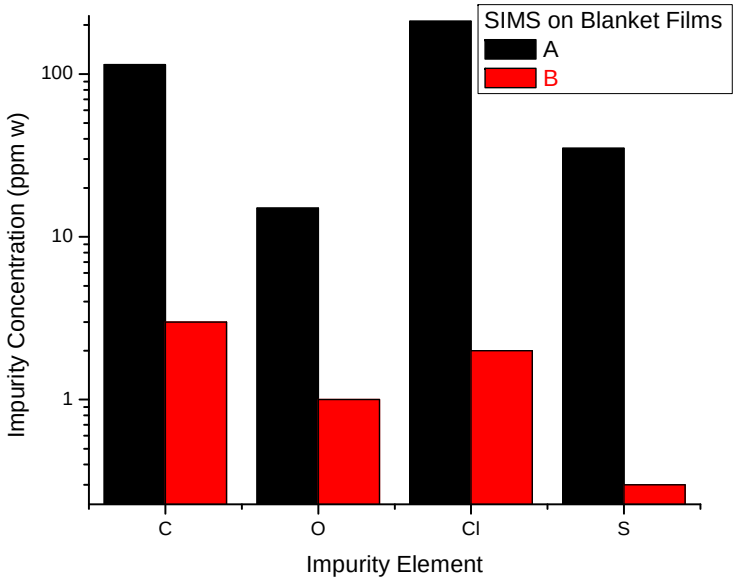
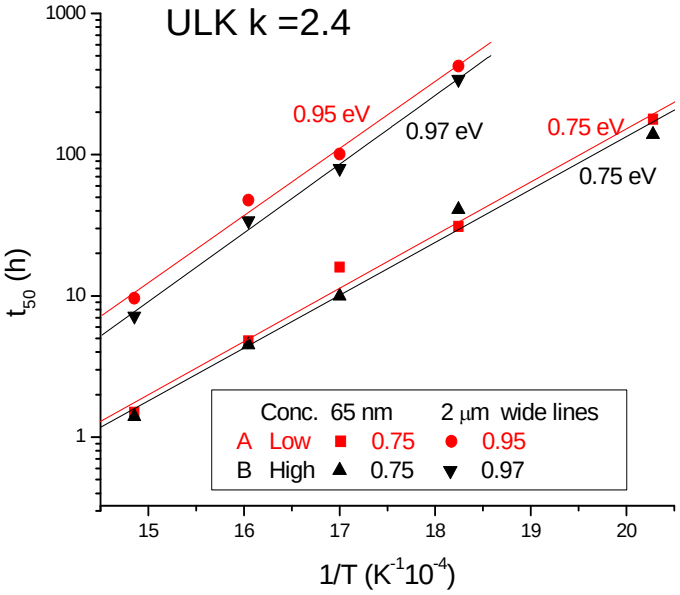
Non-metallic Impurities

- Observed **no** significant EM difference between two chemistries with different impurity concentrations (confirmed by SIMS on blanket wafer or line)
- ECD Cu **1.1** eV vs. CVD Cu **0.8** eV on 2 μm wide lines (Hu&Luther, Mat. Chem. and Phys. 1995).
  - **CVD Cu**: **Polycrystalline** line - **GB** diffusion dominated; Q=0.8 eV
    - Consistent with Cu **GB diffusion activation energy**(*Surholt & Herzig, Acta mater. '97)*
    - **Same Q** obtained from ECD Cu **fine grain size** line (Hu et al. IITC 2007)
  - **Plated Cu**: Abnormal Cu grain growth resulted in a **near bamboo** line structure
    - Mass flow controlled by the slow interface diffusivity not GB

➢ **Microstructure ~ bamboo grain** is the **key for superior ECD_Cu** thin film lines





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Metallic Impurities - EM Cu Alloy

- Cu–**GB** and/or Cu-$SiC_xN_yH_z$ **interface** diffusivities determined mass flow
- Literature reported: Ti, Al, Co, Zr, Sn, In, Pd, Mg, Ag, etc. enhance EM lifetimes
  - ✓Michael & Kim, 2001 reported Al increases Cu grain boundary diffusion
  - ✓Hu et al., 1995 reported Mg degrades Cu lifetimes

➢Impurity increases Cu resistivity

Solubility limit @ 400°C	**Resistivity at%**	**Pin Cu GB Diffusion**
–Pd > 20 at.%	0.9 μΩ-cm	Yes
–Al ~ 20 at.%	0.95 μΩ-cm	No
–Sn ~ 7 at%	3.1 μΩ-cm	Yes
–Mg ~ 3 at.%	0.8 μΩ-cm	No
–Ti < 0.3 at.%	16 μΩ-cm	Yes
–Co ~ 0.04-.1 at.%	6.9 μΩ-cm	No
–Zr ~ 0		Yes
–Ru ~ 0		No
–Ta ~ 0		No

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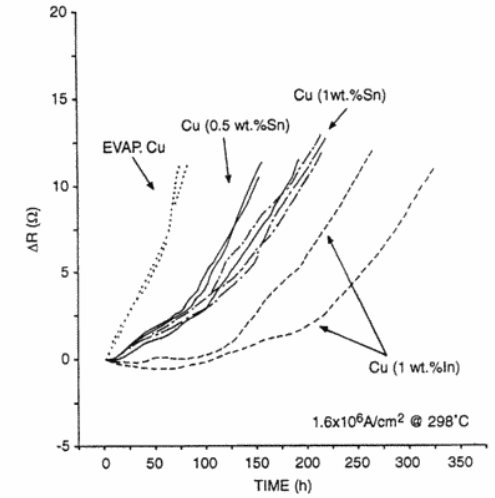
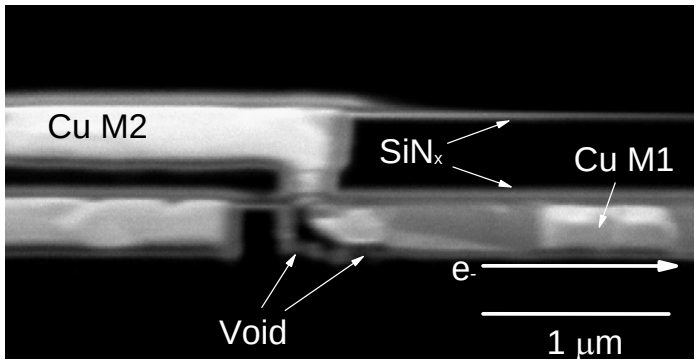
Solute Effect

- Early work on metallic impurities:
  - Ion milled Metal lines: Ta/Cu, Cu(Mg), Cu(Sn), Cu(In), or Cu(Zr)/Ta (Hu et al. TSF('95), US 7090710)
    - Lifetimes degraded by Mg
    - Lifetime and EM activation energy increased by Sn, In, Zr
  - Damascene Cu(Ti), Cu(Zr), Cu(In)
    - Zr, Ti enhanced Cu lifetimes and activation energies (Hu et al, Micro. Eng. (2006))
    - In **degraded** lifetime if Ta liner was contaminated
  - Lift-off Ti(Ta) liner/Cu line on W (US 6503641)
    - Alloy liner increase lifetime and activation energy





Fast diffusion along Ta/Cu interface
Heavily contaminated Ta

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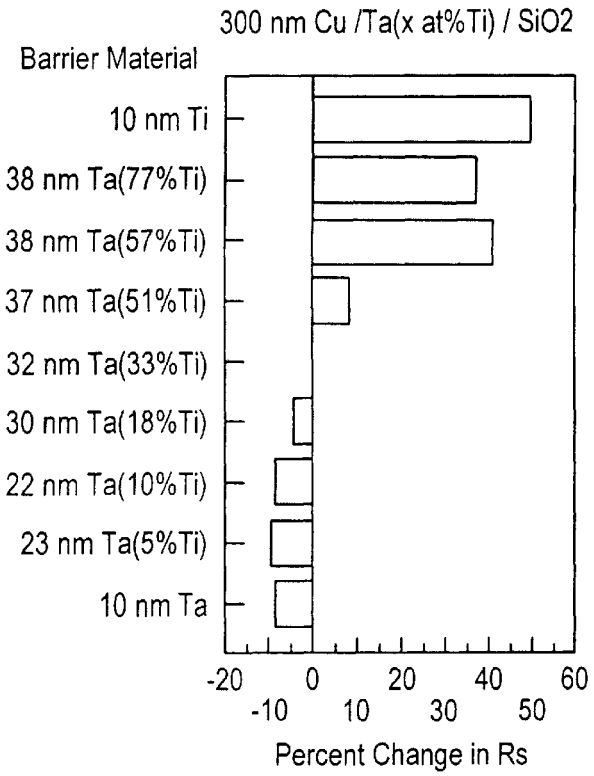
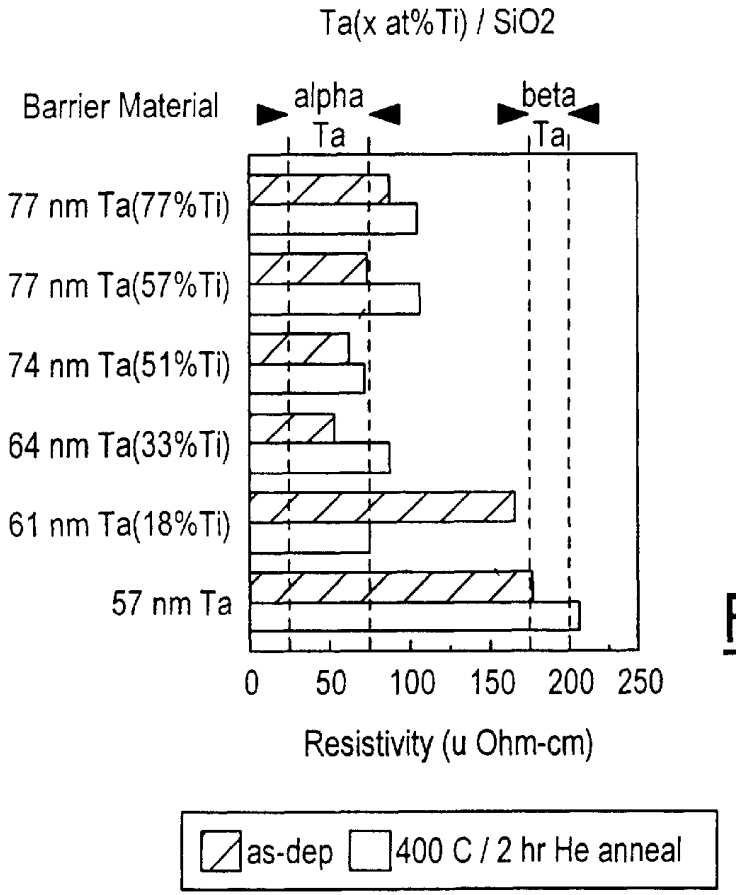
Effect of Ta(Ti) Liner on Cu Resistivity

- Annealed at 400°C for 2h
  - Reactions of Ti/Cu: TiCu and $TiCu_3$ (Hu, et al. MRS. 1986)
  - Sharply increased Cu ρ for Ti > 33%
  - Liner ρ dropped as Ti > 33%, more fractions of α-Ta





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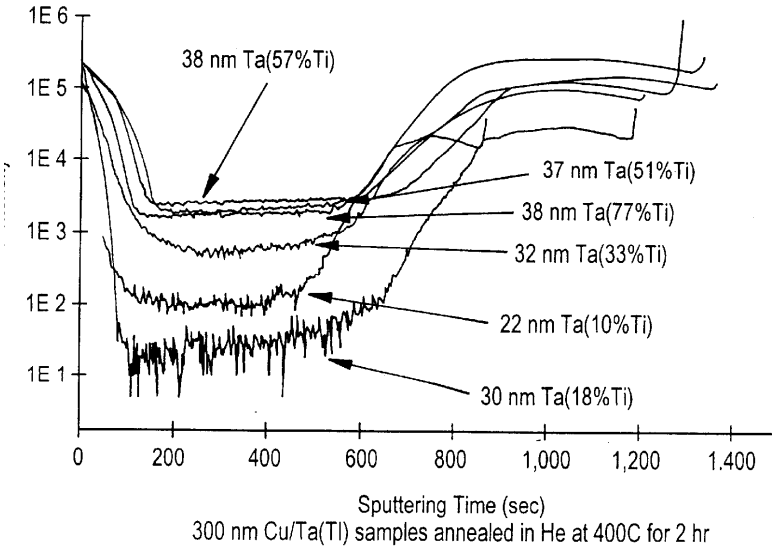
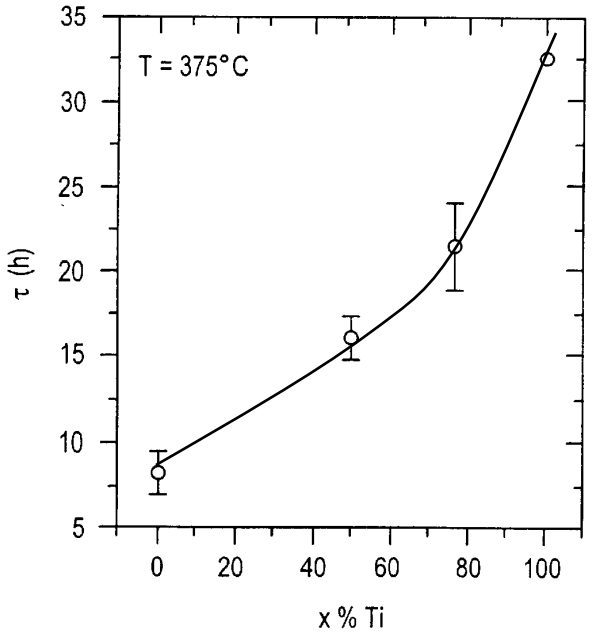
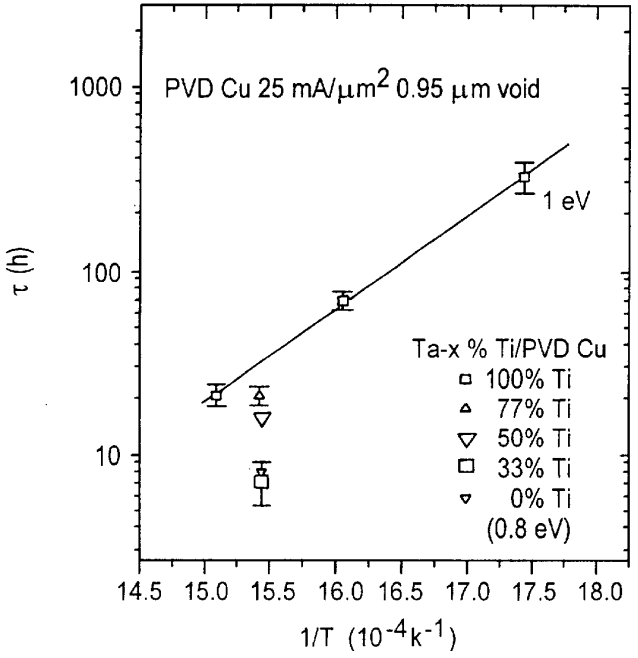
Effect of Ti(Ta) Alloy Liner on Cu EM

- Increase Ti conc. in Ta(Ti) liner on PVD polycrystalline Cu lines
  - Amount Ti in Cu increased
  - Enhanced factor increased
  - GB_Q increased from **0.8 to 1 eV**
- Ta(Ti): Lower manufacture **cost** and **liner** ρ
- With reduced BEOL thermal budget
  - Can cut down Cu resistivity increase and improve lifetime



300 nm Cu/Ta(TI) samples annealed in He at 400C for 2 hr





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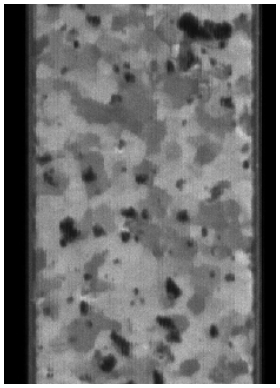
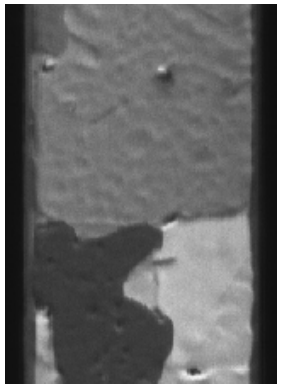
Cu microstructure Variation Obtained by Adjusting Fabrication Steps

- Wafer A: Cu CMP performed right after Cu electroplating with post Cu deposition anneal omitted → Fine grain
- Wafers B: Cu CMP processing after a 100°C anneal, similar microstructure → Large grain

Wafer A



Wafer B



- **Varied Cu grain size**
  - Polycrystalline: GB study
  - Bamboo-like: Interface study

Hu et al. IITC '07

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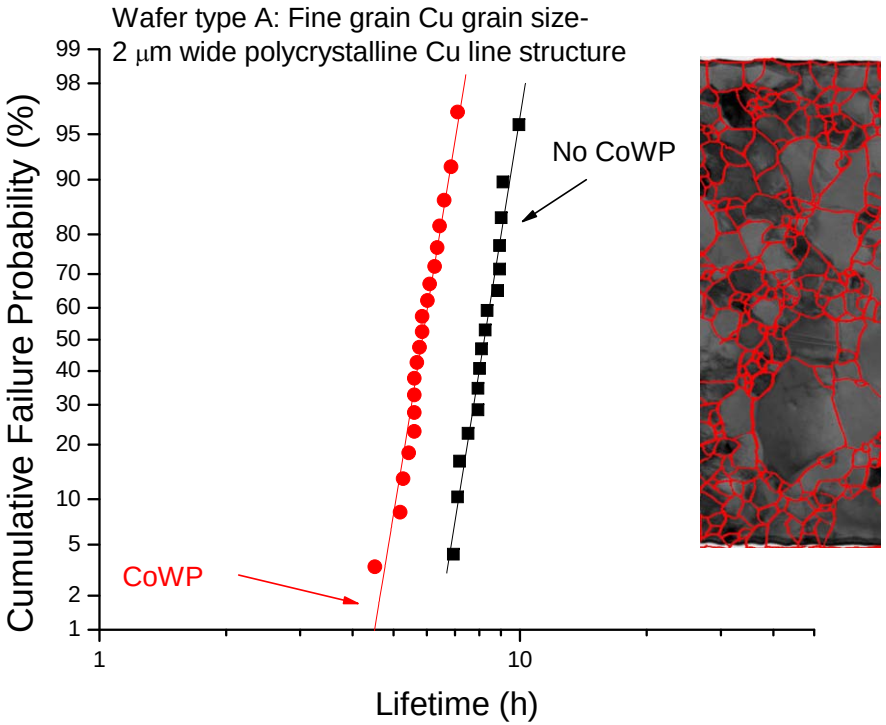
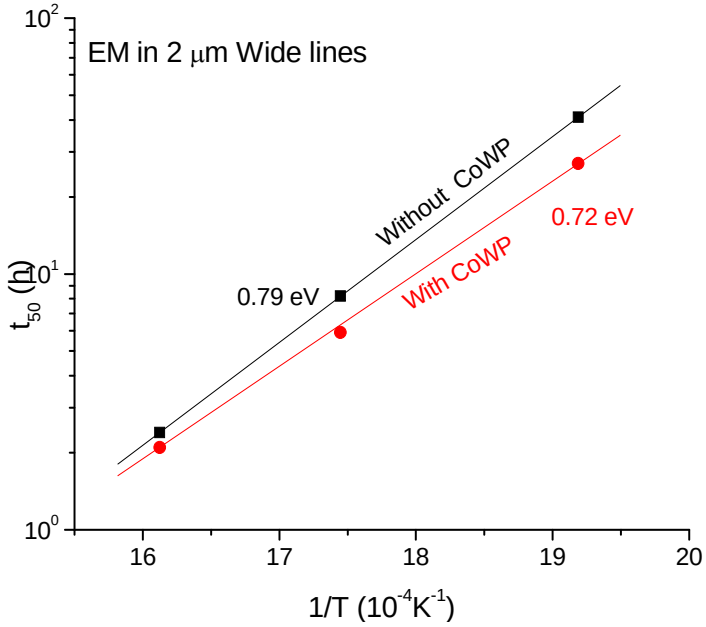
Effect of Co on Cu GB Diffusion

- CoWP cap greatly improved EM lifetime in near bamboo-like line
- Skip pre-CMP anneal wafer had GB continuous network path
- Samples annealed at 400°C for 2h allowed Co diffused into Cu GB
  - **No EM** lifetime enhancement





- CoWP shuts down Cu interfacial, **not GB diffusions**
  - GB diffusion activation energy can be **directly** measured: ~ **0.72eV to 0.79eV**
  - Co has **no effect, or reduced** GB diffusion activation energy

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Solute Effect: Al

1) Standard EM test structure on 65 nm wide lines
   - 1% Al alloy seed
2) Cu(Al) Drift velocity
   - With or without post plated Cu 100^{o}C anneal
     - 1.5 μm wide lines: **Polycrystalline** and **near bamboo** structures
   - 1% and 2 at. % Al
   - SEM images: Void, hillock, grain size

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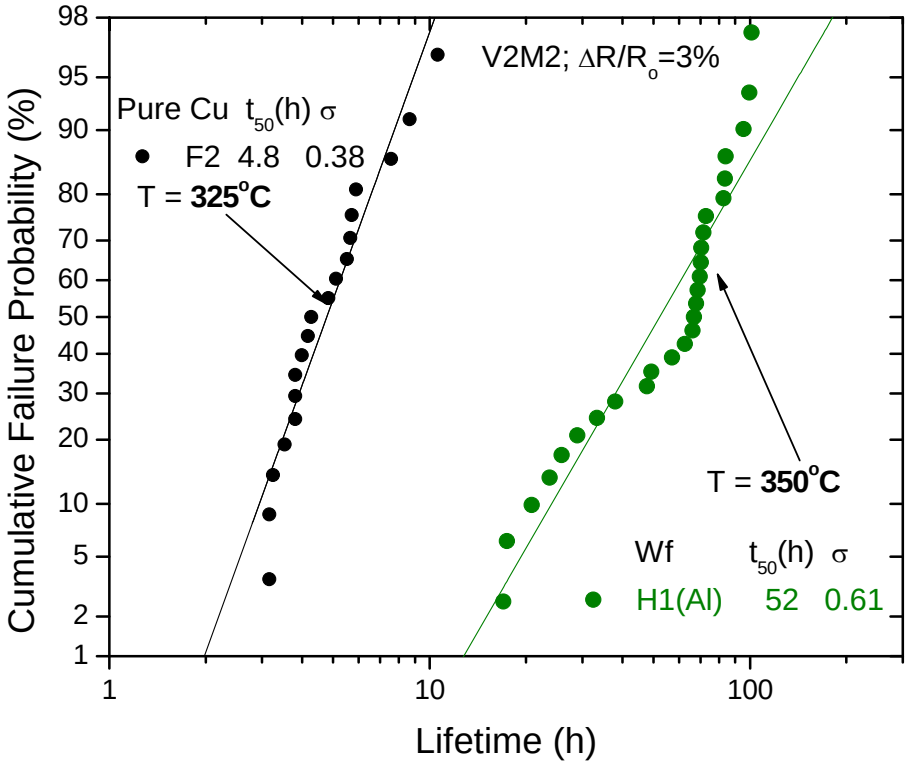
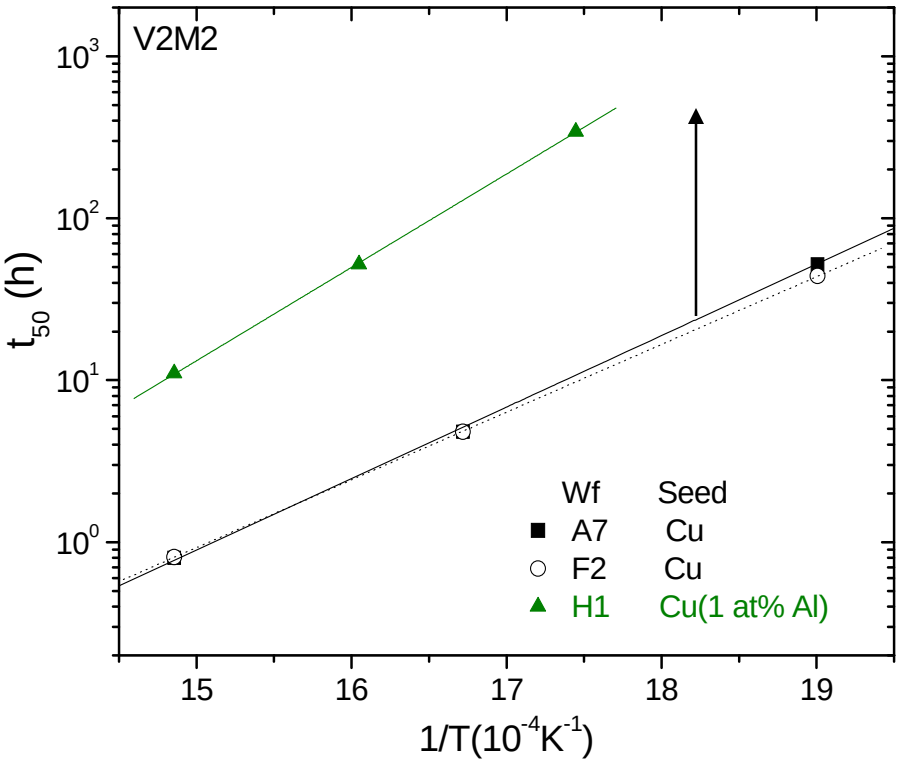
EM in 65 nm Wide Cu Alloy Line





- **1% Al** alloy seed in 65 nm wide line
  - Significantly **enhanced** EM lifetimes
    - Increased EM activation energy from **0.85 to ~ 1.1 eV**
    - **Similar results obtained by** Yokogawa, Tsuchiya: JAP('07)

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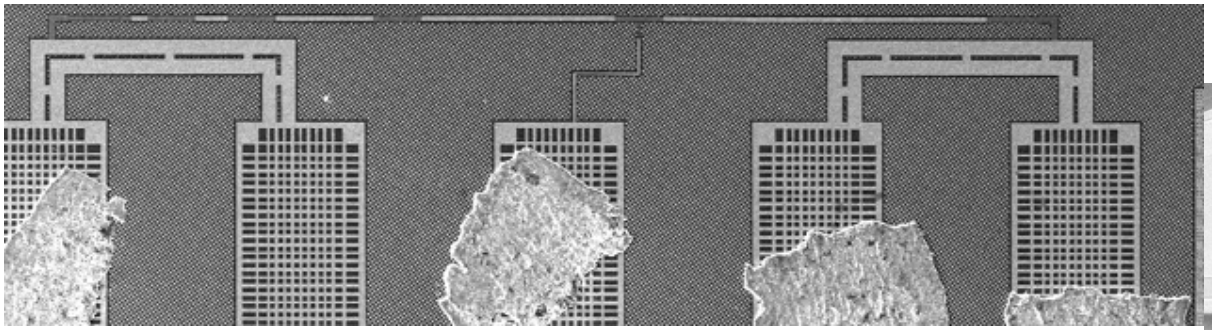
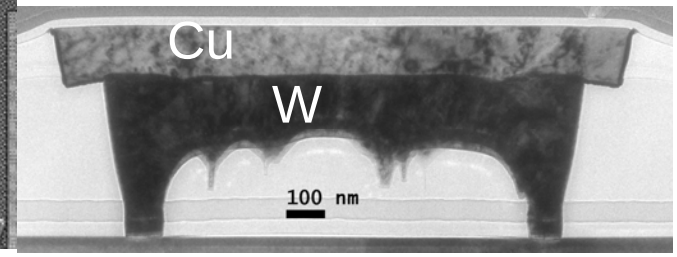
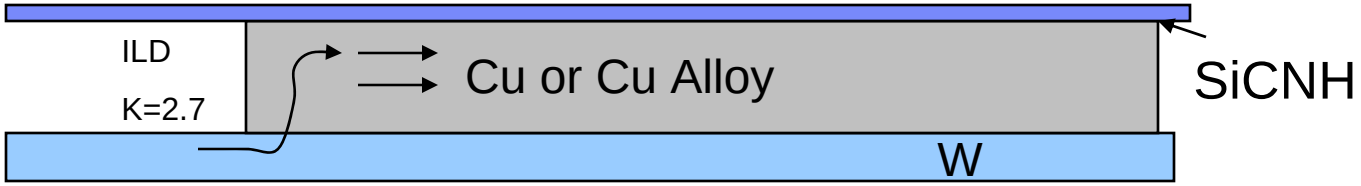
EM Drift Velocity Experiment

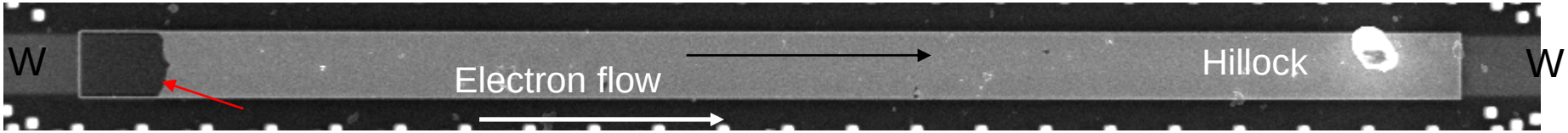
- **Cu line segments of 5, 10, 30, 60, 100 μm long on a continue W line**
- **Fundamental understanding of EM mass flow on 1.5μm wide line**





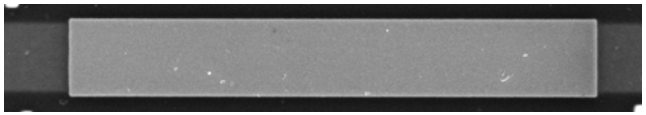


- Voids near at the cathode end and hillocks around at anode end of the line



Marker velocity

- No EM damage observed in 5 and 10 μm wide line (Blech length)



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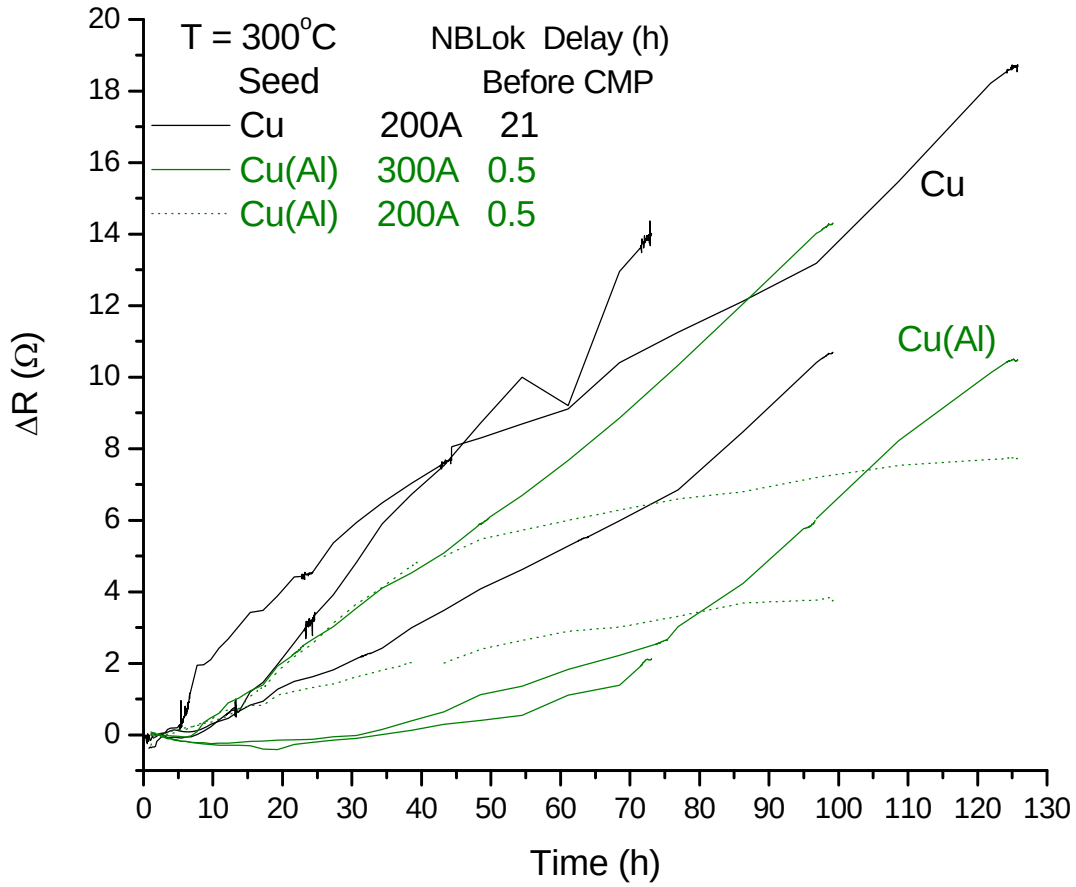
EM Cu(1% Al) Drift Velocity

Resistance Technique: 1% Al alloy seed



Wf A: Samples were skipped post plated Cu 100°C annealing

- 1% Al alloy seed in the polycrystalline (**fine grain size)** lines
  - Mass flows alone grain boundaries
  - Similar EM resistance degradation and void length
    - Impurity, Al, had little or no effect on Cu GB

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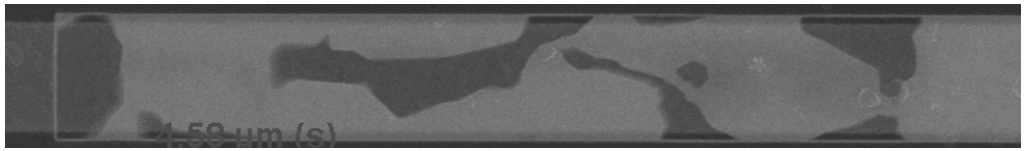
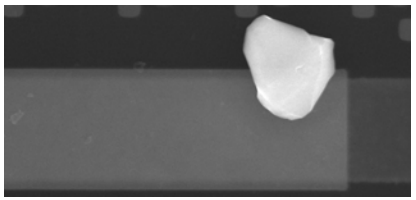
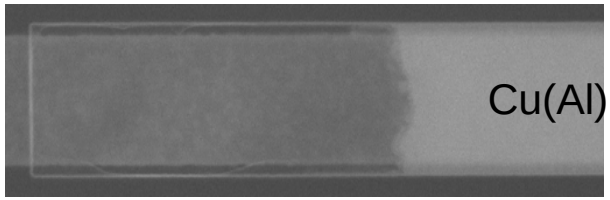
Void Growth: Effect of Impurity and Microstructure

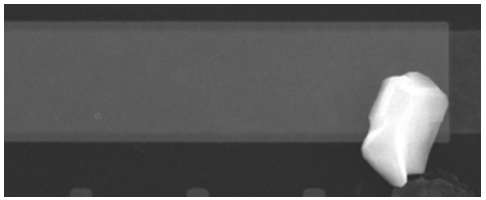
- Cu-Fine Grain : T = 250°C, t = 453h

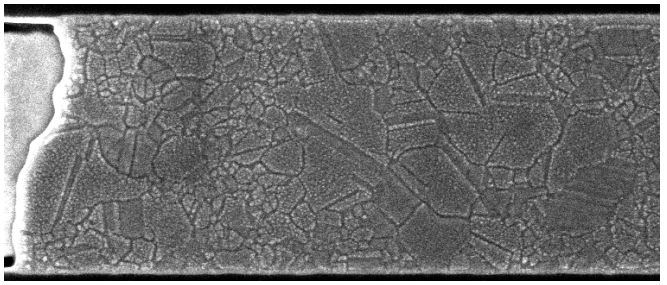




- Cu(1% Al) Fine Grain: Void volume in Cu(Al) > pure Cu







- Skip POR post plated Cu anneal
  - Fine grains mixed with some large grains

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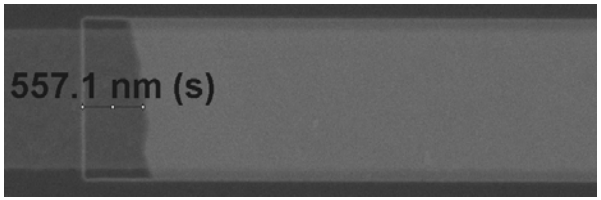
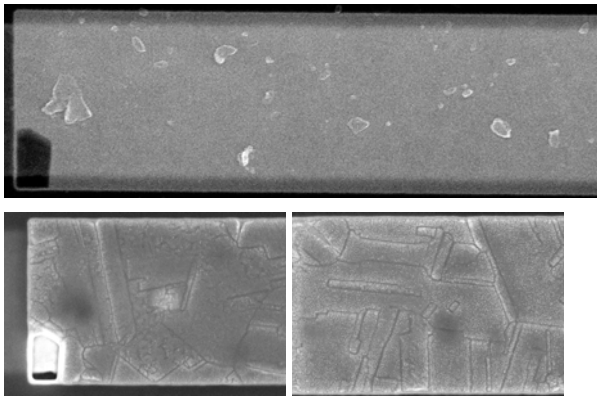
Void Growth: Impurity and Bamboo Grain

T = 250°C, t = 453h

- Cu-100°C Anneal (Wafer B type)
  - Large Cu grain



- Cu(1% Al)-100°C Anneal (B type)
  - ➢ Large Cu grain
  - ➢ Smaller void growth rate



- ❑ 100°C anneal after Cu plating
  - ➢ Large **bamboo-like** grains
- ❑ Compared void growth from large and fine Cu grain samples

➔ Al mitigated interface and not GB diffusion

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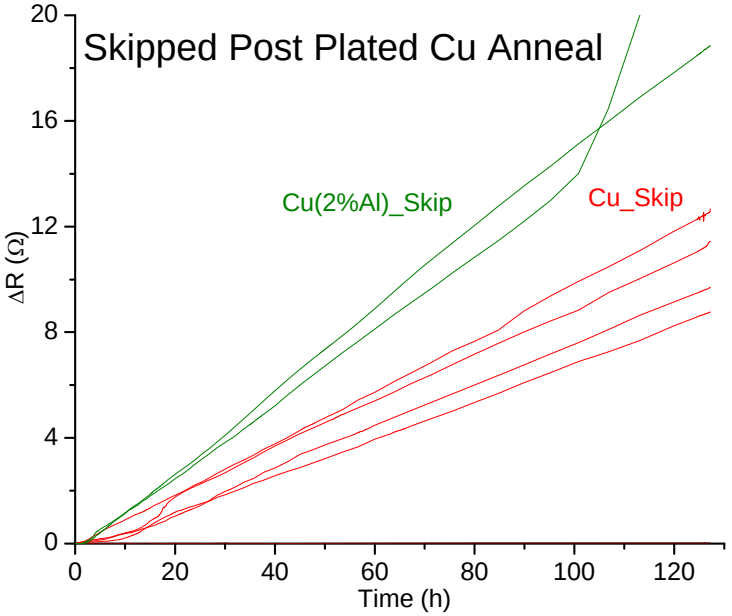
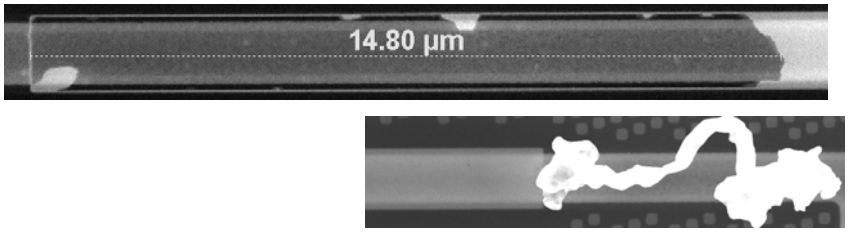
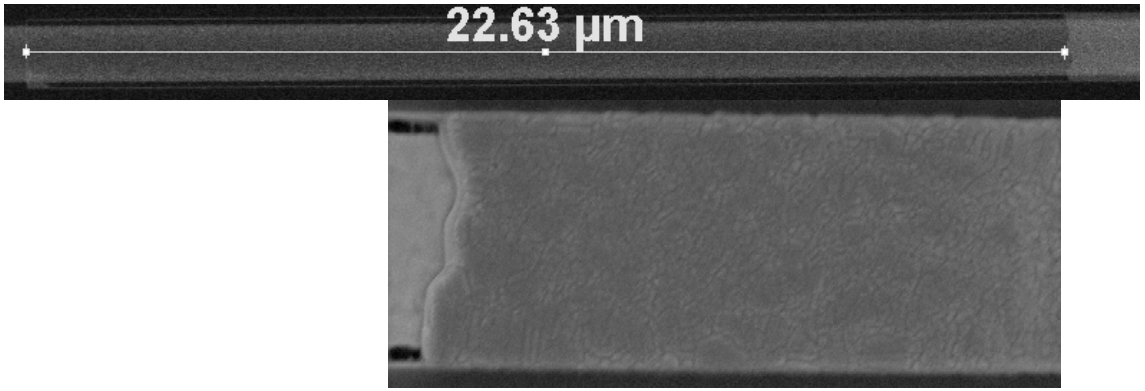
Fine Grain Cu: Solute effect on Cu GB diffusion, Cu(2%Al) seed



❑Cu fine grain



❑Cu(2%Al) fine grain



- ❑Fine Cu grain size obtained by **skipping post plated Cu anneal**
- ❑2%Al alloy seed on 1.5 µm wide polycrystalline Cu lines
  - ❖GB diffusion dominated: Void growth rate Cu(Al) > Cu
  - ❖Al enhanced Cu void growth rate in polycrystalline line
    - ❖Agrees with N.L .Michael, C.U. Kim. J. Appl. Phys. 2001
  - ❖Al increases Cu grain boundary diffusivity

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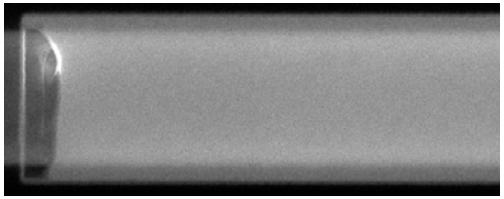
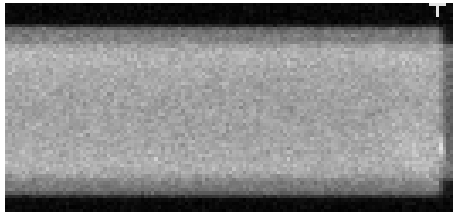
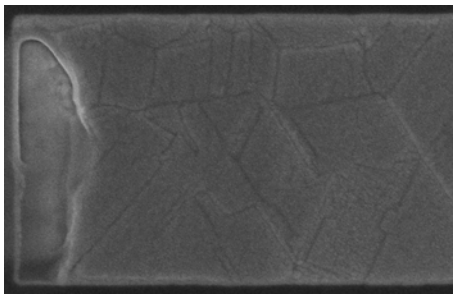
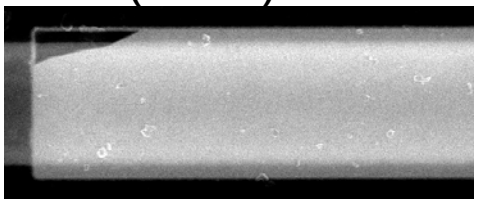
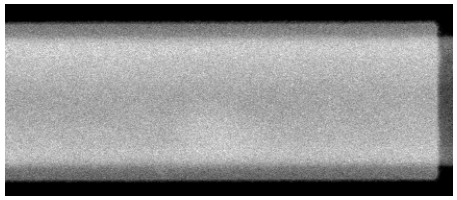
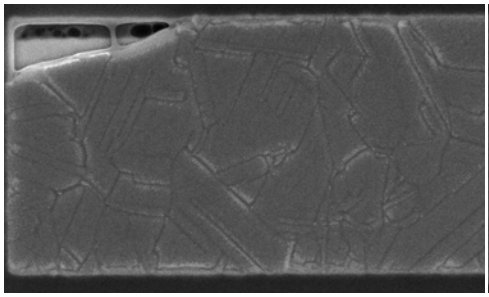
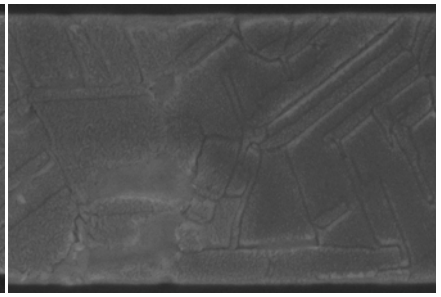
EM Cu Alloy Drift Velocity

Void Growth: **100ºC annealed** samples before CMP

- Pure Cu

- Cu(**2%Al**) seed

- 2%Al alloy seed: POR Anneal before CMP
  - **Near bamboo-like** lines: Interface diffusion dominated
    - Void growth rate Cu >> Cu(2%Al)
    - Impurity, Al, **decreased** Cu interface diffusion

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Effect of non-metallic and metallic impurities on Cu EM

- Observed no difference between high and low non-metallic impurities **Cl, C, S, O**
  - **Microstructure** plays the key role in the superiority of **ECD-Cu** to CVD or PVD
- Ti(Ta) liner
  - Improved PVD polycrystalline Cu line lifetimes
  - Increased EM Cu GB Q_{EM} 0.8 to 1 eV
- In, Zr, Sn increased Cu lifetime and Q
  - However, **In** increased void growth rate if Ta was heavily contaminated
- 1%Al seed for 65 nm wide lines
  - Enhanced EM lifetimes/increased EM Q_{EM} from 0.85 to **1.1 eV**
- 1.5 to 2 μm wide polycrystalline lines
  - Ti, Sn, Zr, In **reduced** Cu GB diffusivity
  - Co has no effect in Cu GB diffusion
  - **Al, Mg** enhanced Cu **GB** diffusivity
    - Al could reduced lifetime enhancement for 22 nm and beyond
  - Impurities, Al, Ti, Zr, Sn, Co **mitigated** Cu interface diffusion
    - **Enhanced** Cu lifetimes for near bamboo-like or bamboo-polycrystalline
  - Oxidized alloy wafers dramatically degraded Cu lifetimes

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